

L Number	Hits	Search Text	DB	Time stamp
1	28988	passivation near6 (film or layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 14:56
2	280903	(active or semiconductor) near6 layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 14:58
3	1	(passivation near6 (film or layer)) near6 ((active or semiconductor) near6 layer) near6 pattern\$3 near6 simultaneous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 15:05
4	1412771	passivat\$3 or insulat\$3 or planariz\$5 or overcoat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 15:09
5	320013	(active adj layer) or (amorphous impurity semiconductor) near5 (layer region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 15:12
6	1431012	simultaneously or concurrently	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 15:16
7	370970	mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 15:18
8	1	(passivation near6 (film or layer)) and ((active or semiconductor) near6 layer) and ((passivation near6 (film or layer)) near6 ((active or semiconductor) near6 layer) near6 pattern\$3 near6 simultaneous) and (passivat\$3 or insulat\$3 or planariz\$5 or overcoat\$3) and ((active adj layer) or (amorphous impurity semiconductor) near5 (layer region)) and (simultaneously or concurrently) and mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 15:19
9	19084	(passivat\$3 or insulat\$3 or planariz\$5 or overcoat\$3) and ((active adj layer) or (amorphous impurity semiconductor) near5 (layer region)) and (simultaneously or concurrently) and mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 15:42
10	28	(passivat\$3 or insulat\$3 or planariz\$5 or overcoat\$3) near6 ((active adj layer) or (amorphous impurity semiconductor) near5 (layer region)) near6 (simultaneously or concurrently) near6 mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 15:33
11	2	(passivation near6 (film or layer)) near6 ((active adj layer) or (amorphous impurity semiconductor) near5 (layer region)) near6 (simultaneously or concurrently) near6 mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 15:40
12	1	"10/028289"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 15:37

13	103525	(silicon adj nitride) or benzocyclobutene	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 15:40
14	5	((silicon adj nitride) or benzocyclobutene) near6 ((active adj layer) or (amorphous impurity semiconductor) near5 (layer region)) near6 (simultaneously or concurrently) near6 mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 15:40
15	66	(passivat\$3 or insulat\$3 or planariz\$5 or overcoat\$3) and ((active adj layer) or (amorphous impurity semiconductor) near5 (layer region)) and (simultaneously or concurrently) and (four adj mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 15:44
16	27858	gate near6 insulating near6 layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 15:47
17	1050	auxiliary near6 capacit\$3 near6 electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 16:00
18	80613	capacit\$3 near6 electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 16:02
19	22331	pixel near6 electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 16:04
20	101	(pixel near6 electrode) near6 (contact\$3 or connect\$3) near6 (auxiliary near6 capacit\$3 near6 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 16:23
21	2	((active adj layer) or (amorphous impurity semiconductor) near5 (layer region)) near6 (gate near6 insulating near6 layer) near6 (capacit\$3 near6 electrode) near6 (auxiliary near6 capacit\$3 near6 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 16:06
22	36	((pixel near6 electrode) near6 (contact\$3 or connect\$3) near6 (auxiliary near6 capacit\$3 near6 electrode)) and @py<2000	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 16:09
23	0	(pixel near6 electrode) adj (contact\$3 or connect\$3) adj (auxiliary near6 capacit\$3 near6 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 16:12
24	57	(gate near6 insulating near6 layer) near6 (overlay\$5 or overlap\$5 or above) near6 (capacit\$3 near6 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 16:27
25	1	((pixel near6 electrode) near6 (contact\$3 or connect\$3) near6 (auxiliary near6 capacit\$3 near6 electrode)) and ((gate near6 insulating near6 layer) near6 (overlay\$5 or overlap\$5 or above) near6 (capacit\$3 near6 electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 16:31

26	476	(gate near6 insulating near6 layer) near6 (capacit\$3 near6 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 16:26
27	0	(gate near6 insulating near6 layer) adj (overlay\$5 or overlap\$5 or above) adj (capacit\$3 near6 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 16:27

L Number	Hits	Search Text	DB	Time stamp
1	2064	storage near6 capacitor near6 region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 17:28
2	30	gate near6 insulat\$5 near6 (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 16:53
3	69938	gate near6 insulat\$5 near6 (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 16:55
4	1	(gate near6 insulat\$5 near6 (layer or film)) near6 (overlay\$3 or cover\$3 or overlap\$3) near6 (storage near6 capacitor near6 region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 17:25
5	73	(gate near6 insulat\$5 near6 (layer or film)) near6 (storage near6 capacitor near6 region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 17:00
6	22331	pixel near6 electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 16:58
7	1516	auxiliary near6 capacit\$5 near6 electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 17:06
8	33	(pixel near6 electrode) near6 contact\$3 near6 (auxiliary near6 capacit\$5 near6 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 17:02
9	0	((gate near6 insulat\$5 near6 (layer or film)) near6 (storage near6 capacitor near6 region)) and ((pixel near6 electrode) near6 contact\$3 near6 (auxiliary near6 capacit\$5 near6 electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 17:00
10	1109	(gate near6 insulat\$5 near6 (layer or film)) and (storage near6 capacitor near6 region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 17:01
11	1	((pixel near6 electrode) near6 contact\$3 near6 (auxiliary near6 capacit\$5 near6 electrode)) and ((gate near6 insulat\$5 near6 (layer or film)) and (storage near6 capacitor near6 region))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 17:01
13	0	((gate near6 insulat\$5 near6 (layer or film)) near6 (storage near6 capacitor near6 region)) and ((pixel near6 electrode) near6 (contact\$3 or connect\$3) near6 (auxiliary near6 capacit\$5 near6 electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 17:03

14	96189	capacit\$5 near6 electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 17:10
15	1379	((pixel near6 electrode) near6 (contact\$3 or connect\$3) near6 (capacit\$5 near6 electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 17:11
16	25	((gate near6 insulat\$5 near6 (layer or film)) near6 (storage near6 capacitor near6 region)) and ((pixel near6 electrode) near6 (contact\$3 or connect\$3) near6 (capacit\$5 near6 electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 17:11
17	268	(gate near6 insulat\$5 near6 (layer or film)) near6 (overlay\$3 or cover\$3 or overlap\$3) near6 (capacit\$5 near6 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 17:26
18	774	(storage near6 capacitor near6 region) near6 (capacit\$5 near6 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 17:28
19	466	(gate near6 insulat\$5 near6 (layer or film)) and ((storage near6 capacitor near6 region) near6 (capacit\$5 near6 electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 17:29
20	98	((pixel near6 electrode) near6 (contact\$3 or connect\$3) near6 (capacit\$5 near6 electrode)) and ((gate near6 insulat\$5 near6 (layer or film)) and ((storage near6 capacitor near6 region) near6 (capacit\$5 near6 electrode)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 17:29
21	21	((((pixel near6 electrode) near6 (contact\$3 or connect\$3) near6 (capacit\$5 near6 electrode)) and ((gate near6 insulat\$5 near6 (layer or film)) and ((storage near6 capacitor near6 region) near6 (capacit\$5 near6 electrode)))) and @py<2000	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/16 17:29